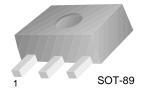


KSB1121

High Current Driver Applications

- Low Collector-Emitter Saturation Voltage
- Large Current Capacity and Wide SOA
- Fast Switching Speed
- Complement to KSD1621



1. Base 2. Collector 3. Emitter

PNP Epitaxial Planar Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current	-2	Α
	Collector Power Dissipation	500	mW
P _C P _C *		1.3	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

^{*} Mounted on Ceramic Board (250mm2 x 0.8mm)

$\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} = 25 ^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I_{C} = -10 μ A, I_{E} = 0	-30			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -1 \text{mA}, I_B = 0$	-25			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = -10\mu A, I_C = 0$	-6			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = -20V, I_{E} = 0$			-100	nA
I _{EBO}	Emitter Cut-off Current	$V_{BE} = -4V, I_{C} = 0$			-100	nA
h _{FE1}	DC Current Gain	V _{CE} = -2V, I _C = -0.1A	100		560	
h_{FE2}		$V_{CE} = -2V, I_{C} = -1.5A$	65			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = -1.5A, I _B = -75mA		-0.35	-0.6	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = -1.5A, I _B = -75mA		-0.85	-1.2	V
f _T	Current Gain Bandwidth Product	$V_{CE} = -10V, I_{C} = -50mA$		150		MHz
C _{ob}	Output Capacitance	V _{CB} = -10V, I _E =0, f=1MHz		32		pF
t _{ON}	* Turn On Time	$V_{CC} = -12V, V_{BE} = -5V$		60		ns
t _{STG}	* Storage Time	$I_{B1} = -I_{B2} = -25 \text{mA}$		350		ns
t _F	* Fall time	I_C = -500mA, R_L =24 Ω		25		ns

^{*} Pulse Test: PW≤20μs, Duty Cycle≤1%

h_{FE} Classification

Classification	R	S	Т	U
h _{FE1}	100 ~ 200	140 ~ 280	200 ~ 400	280 ~ 560





 h_{FE} Grade

Typical Characteristics

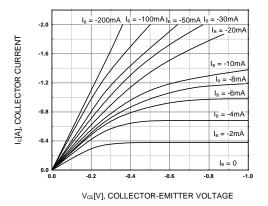


Figure 1. Static Characteristic

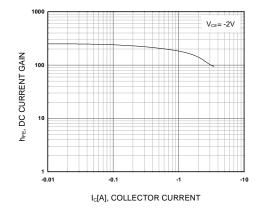


Figure 2. DC current Gain

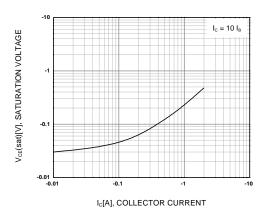


Figure 3. Collector-Emitter Saturation Voltage

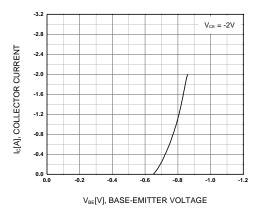


Figure 4. Base-Emitter On Voltage

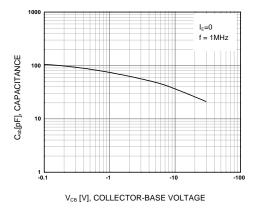


Figure 5. Collector Output Capacitance

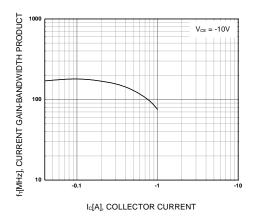
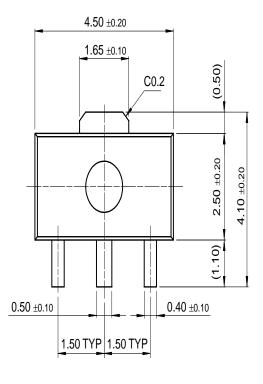


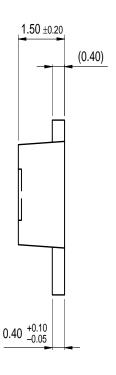
Figure 6. Current Gain Bandwidth Product

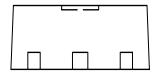
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Package Demensions

SOT-89







Dimensions in Millimeters

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